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N-Channel 80 V (D-S) Power MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ) (TYP.)	I _D (A)	Q _g (TYP.)			
80	1.9 at V _{GS} = 10 V	180	78 nC			

FEATURES

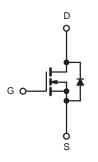
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



APPLICATIONS

- Networking
- · Load Switch





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	80	V		
Gate-Source Voltage	V _{GS}	± 20	v		
Continuous Dunin Courset (T. 150 °C)	T _C = 25 °C	1	180		
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	I _D	115	^	
Pulsed Drain Current (t = 100 μs)	I _{DM}	720	_ A		
Avalanche Current	L = 0.1 mH	I _{AS}	146		
Single Avalanche Energy ^a	L = 0.1 IIII	E _{AS}	618	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	245 ^b	W	
waxiinum rowei bissipation 4	T _C = 100 °C	- rD	93 b	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	62	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.65		

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS ($T_J = 25$ °C	C, unless oth	nerwise noted)					
PARAMETER SYM		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 80 V, V _{GS} = 0 V		-	1	_	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 64 V, V _{GS} = 0 V, T _J = 85 °C	-	-	10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	180	-	-	Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	1.9	2.3	mΩ	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_D = 30 \text{ A}$	-	95	-	S	
Dynamic ^b			•				
Input Capacitance	C _{iss}		-	5580	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 40 \text{ V}, f = 1 \text{ MHz}$	-	885	-		
Reverse Transfer Capacitance	C _{rss}		-	12	-		
Total Gate Charge ^c	Qg		-	78		nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	40	-		
Gate-Drain Charge c	Q_{gd}		-	17	-		
Gate Resistance	R_{g}	f = 1 MHz		2.0		Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	35	-		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_L = 2 \Omega$	-	19	-		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D = 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 3 \Omega$	-	48	-	ns	
Fall Time ^c	t _f		-	29	-	1	
Drain-Source Body Diode Ratings at	nd Characteri	stics ^b (T _C = 25 °C)		<u> </u>			
Continuous Source Current	I _S	T _C = 25 °C	-	-	180	Α	
Pulsed Source Current	I _{SM}		-	-	720	Α	
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1	V	
Reverse Recovery Time	t _{rr}	L = 20 A di/dt = 100 A/···	-	58	-	ns	
Reverse Recovery Charge	Q _{rr}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	80	-	nC	

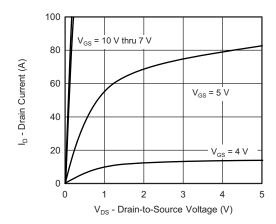
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

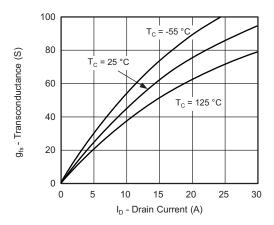
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



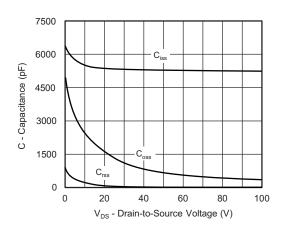
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



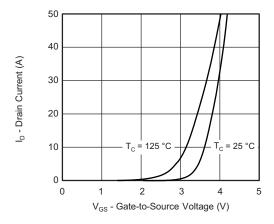
Output Characteristics



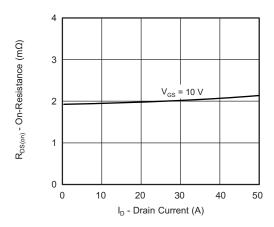
Transconductance



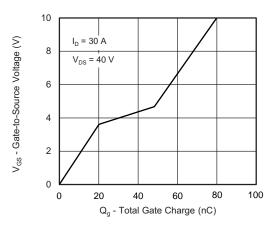
Capacitance



Transfer Characteristics



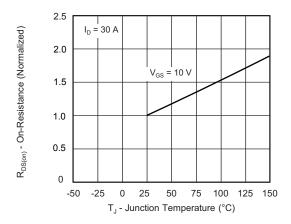
On-Resistance vs. Drain Current



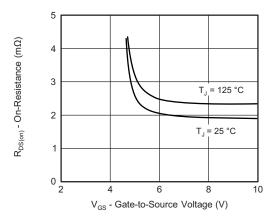
Gate Charge



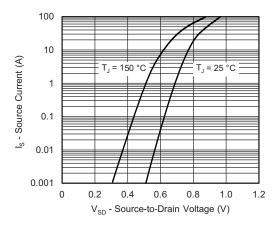
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



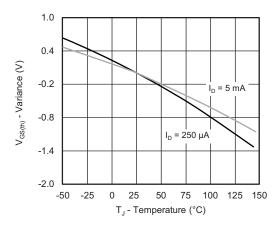
On-Resistance vs. Junction Temperature



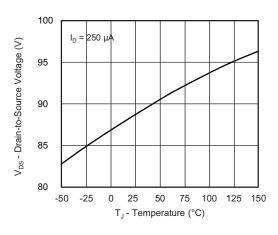
On-Resistance vs. Gate-to-Source Voltage



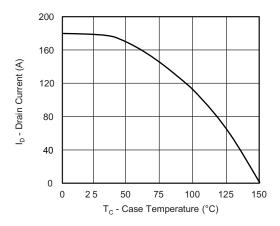
Source Drain Diode Forward Voltage



Threshold Voltage



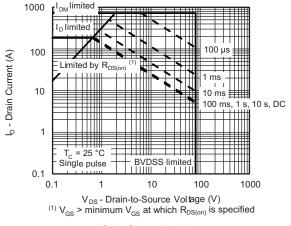
Drain Source Breakdown vs. Junction Temperature



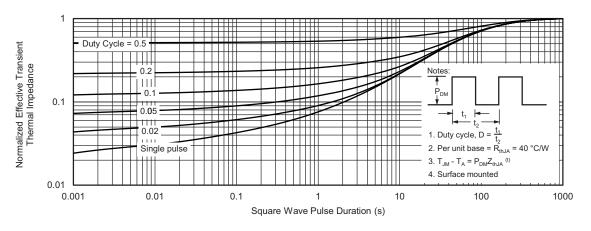
Current De-Rating



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



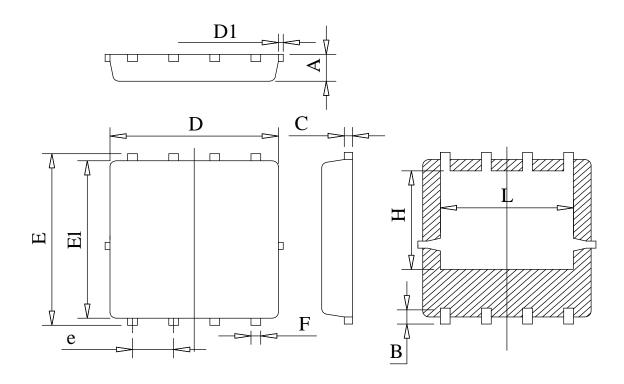
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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